

6-Pin General Purpose Phototransistor Optocoupler

H11A1M

Description

The general purpose optocoupler consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a standard plastic 6-pin dual-in-line package.

Features

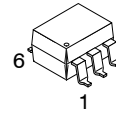
- Minimum Current Transfer Ratio, 50% at $I_F = 10 \text{ mA}$, $V_{CE} = 10 \text{ V}$:
- Safety and Regulatory Approvals:
 - ♦ UL1577, 4,170 VAC_{RMS} for 1 Minute
 - ♦ DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

Applications

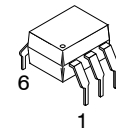
- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs



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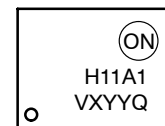


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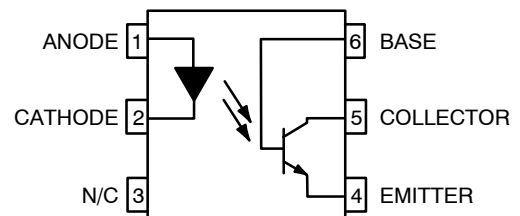
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CASE 646BZ

MARKING DIAGRAM



- ON = Logo
 H11A1 = Specific Device Code
 V = DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
 X = One-Digit Year Code
 YY = Digit Work Week
 Q = Assembly Package Code

SCHEMATIC



ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

H11A1M

SAFETY AND INSULATION RATINGS (As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.)

Parameter		Characteristics
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	<150 V _{RMS}	I–IV
	<300 V _{RMS}	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, V _{IORM} × 1.6 = V _{PR} , Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC	1360	V _{peak}
	Input-to-Output Test Voltage, Method B, V _{IORM} × 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC	1594	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥7	mm
	External Clearance	≥7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥0.5	mm
T _S	Case Temperature (Note 1)	175	°C
I _{S,INPUT}	Input Current (Note 1)	350	mA
P _{S,OUTPUT}	Output Power (Note 1)	800	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	>10 ⁹	Ω

1. Safety limit values – maximum values allowed in the event of a failure.

H11A1M

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Max	Unit
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TOTAL DEVICE

T _{STG}	Storage Temperature	-40 to +125	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
T _J	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
P _D	Total Device Power Dissipation @ T _A = 25°C	270	mW
	Derate Above 25°C	2.94	mW/°C

EMITTER

I _F	DC / Average Forward Input Current	60	mA
V _R	Reverse Input Voltage	6	V
I _{F(pk)}	Forward Current – Peak (300 μs, 2% Duty Cycle)	3	A
P _D	LED Power Dissipation @ T _A = 25°C	120	mW
	Derate Above 25°C	1.41	mW/°C

DETECTOR

V _{CEO}	Collector-to-Emitter Voltage	30	V
V _{CBO}	Collector-to-Base Voltage	70	V
V _{ECO}	Emitter-to-Collector Voltage	7	V
P _D	Detector Power Dissipation @ T _A = 25°C	150	mW
	Derate Above 25°C	1.76	mW/°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

H11A1M

ELECTRICAL CHARACTERISTICS – INDIVIDUAL COMPONENT CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
EMITTER						
V _F	Input Forward Voltage	I _F = 10 mA	–	1.18	1.50	V
I _R	Reverse Leakage Current	V _R = 6.0 V	–	0.001	10	μA

DETECTOR

BV _{CEO}	Collector-to-Emitter Breakdown Voltage	I _C = 1.0 mA, I _F = 0	30	100	–	V
BV _{CBO}	Collector-to-Base Breakdown Voltage	I _C = 100 μA, I _F = 0	70	120	–	V
BV _{ECO}	Emitter-to-Collector Breakdown Voltage	I _E = 100 μA, I _F = 0	7	10	–	V
I _{CEO}	Collector-to-Emitter Dark Current	V _{CE} = 10 V, I _F = 0	–	1	50	nA
I _{CBO}	Collector-to-Base Dark Current	V _{CB} = 10 V	–	–	20	nA
C _{CE}	Capacitance	V _{CE} = 0 V, f = 1 MHz	–	8	–	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS – TRANSFER CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
DC CHARACTERISTICS						
CTR	Current Transfer Ratio, Collector-to-Emitter	I _F = 10 mA, V _{CE} = 10 V	50	–	–	%
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage	I _C = 0.5 mA, I _F = 10 mA	–	–	0.4	V

AC CHARACTERISTIC

T _{ON}	Non-Saturated Turn-on Time	I _F = 10 mA, V _{CC} = 10 V, R _L = 100 Ω (Figure 11)	–	2	–	μs
T _{OFF}	Turn-off Time	I _F = 10 mA, V _{CC} = 10 V, R _L = 100 Ω (Figure 11)	–	2	–	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS – ISOLATION CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{ISO}	Input-Output Isolation Voltage	t = 1 Minute	4170	–	–	V _{ACRMS}
C _{ISO}	Isolation Capacitance	V _{I-O} = 0 V, f = 1 MHz	–	0.2	–	pF
R _{ISO}	Isolation Resistance	V _{I-O} = ±500 VDC, T _A = 25°C	10 ¹¹	–	–	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CURVES

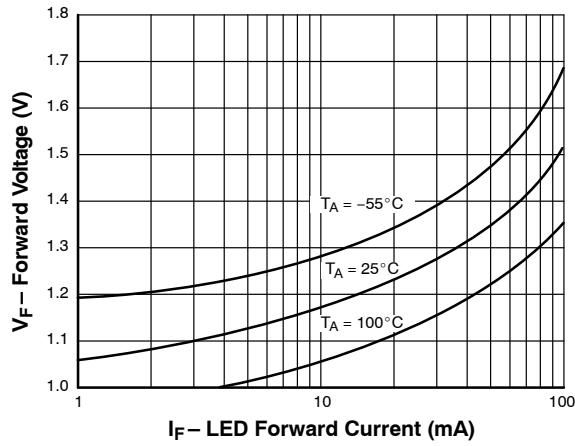


Figure 1. LED Forward Voltage vs. Forward Current

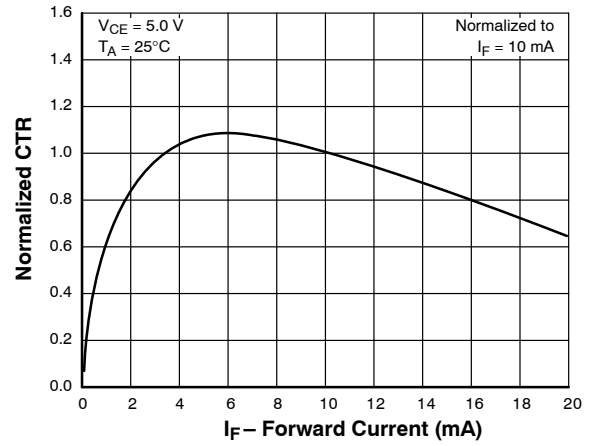


Figure 2. Normalized CTR vs. Forward Current

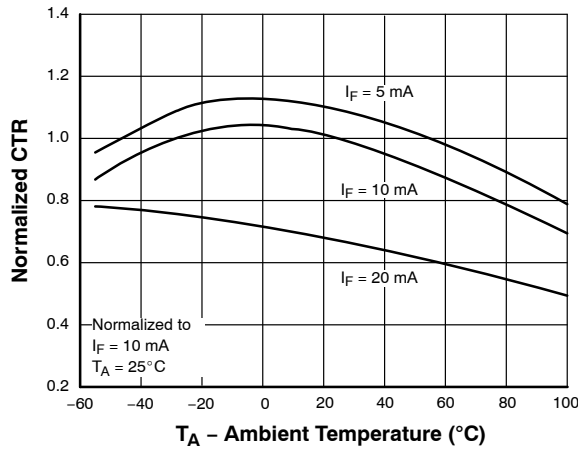


Figure 3. Normalized CTR vs. Ambient Temperature

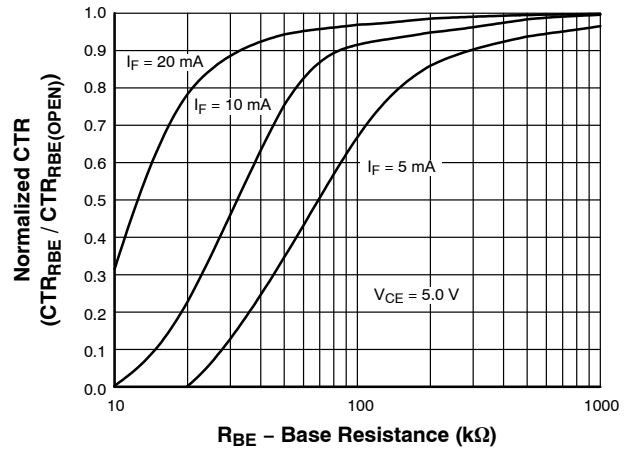


Figure 4. CTR vs. RBE (Unsaturated)

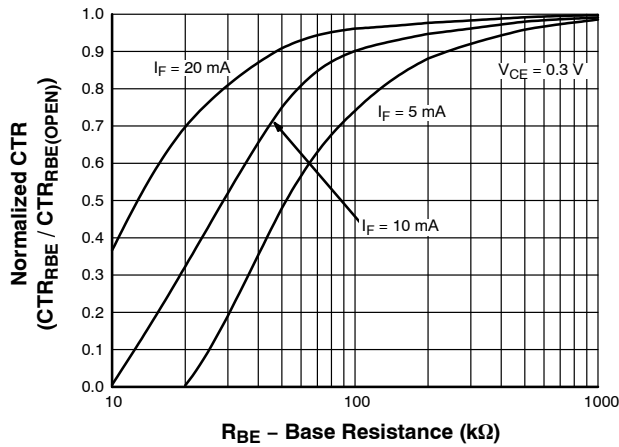


Figure 5. CTR vs. RBE (Saturated)

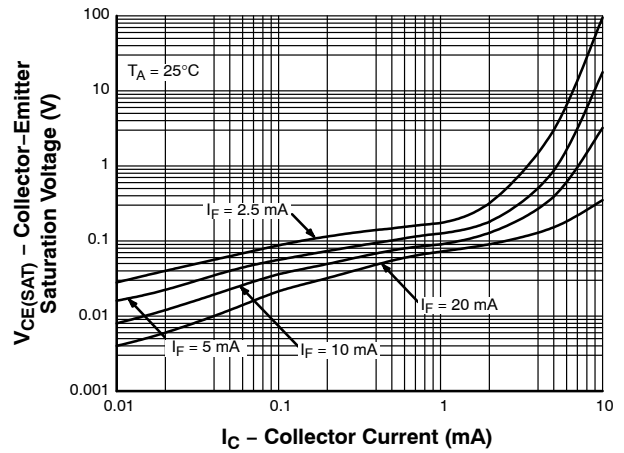


Figure 6. Collector-Emitter Saturation Voltage vs. Collector Current

TYPICAL PERFORMANCE CURVES (continued)

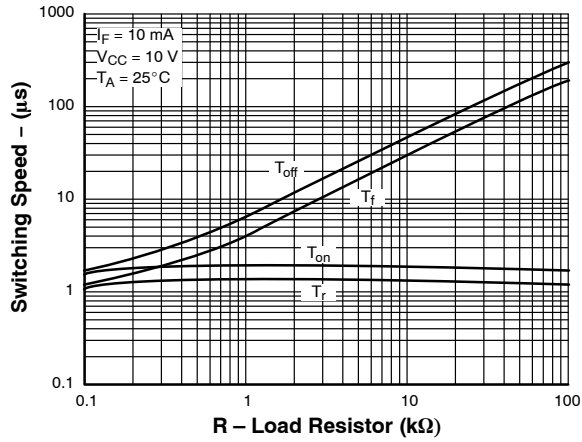


Figure 7. Switching Speed vs. Load Resistor

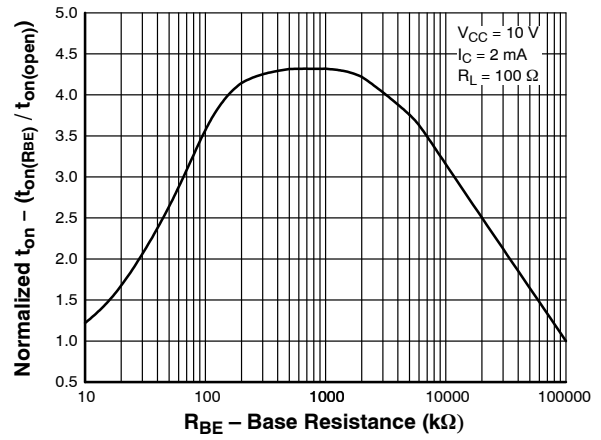


Figure 8. Normalized t_{on} vs. R_{BE}

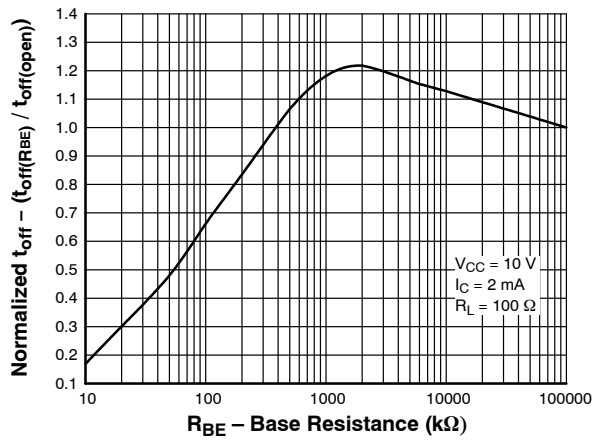


Figure 9. Normalized t_{off} vs. R_{BE}

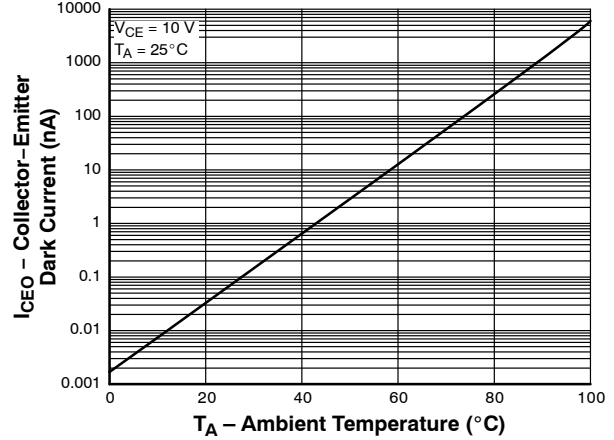


Figure 10. Dark Current vs. Ambient Temperature

SWITCHING TIME TEST CIRCUIT AND WAVEFORMS

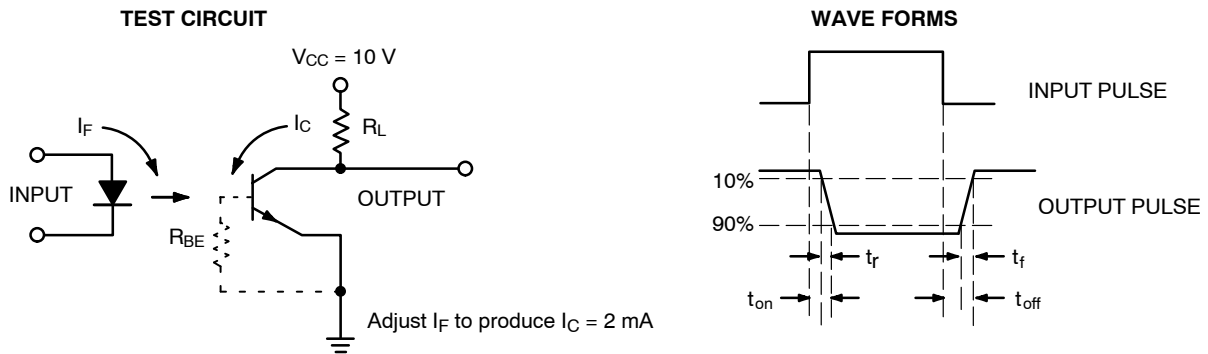


Figure 11. Switching Time Test Circuit and Waveforms

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REFLOW PROFILE

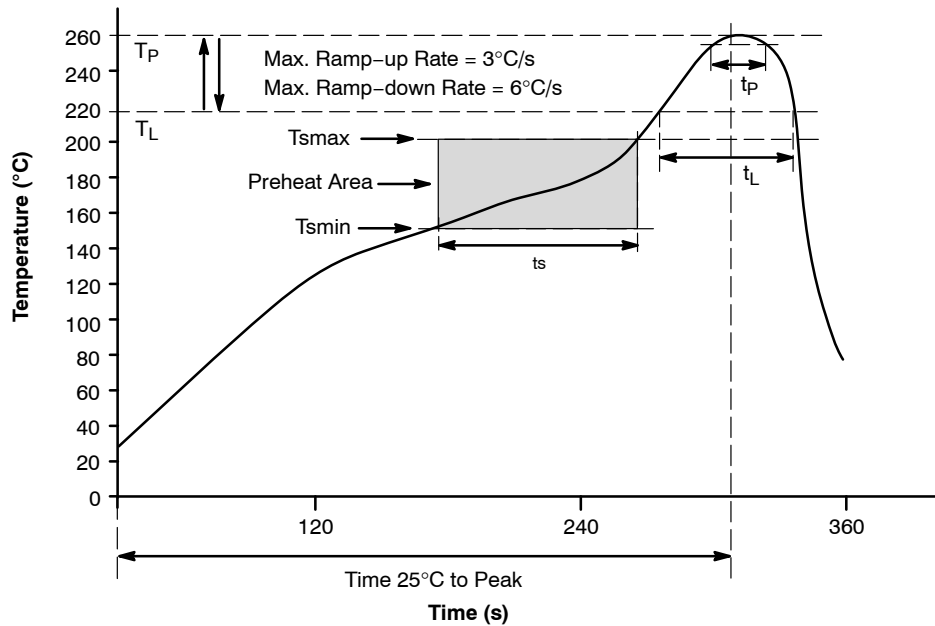


Figure 12. Reflow Profile

REFLOW PROFILE

Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{min})	150°C
Temperature Max. (T _{max})	200°C
Time (t _s) from (T _{min} to T _{max})	60–120 s
Ramp-up Rate (t _L to t _p)	3°C/s max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 s
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _p) within 5°C of 260°C	30 s
Ramp-down Rate (T _P to T _L)	6°C/s max.
Time 25°C to Peak Temperature	8 min max.

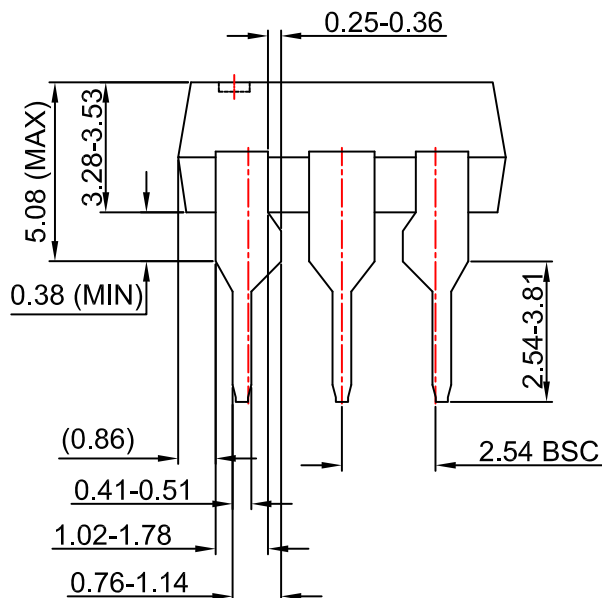
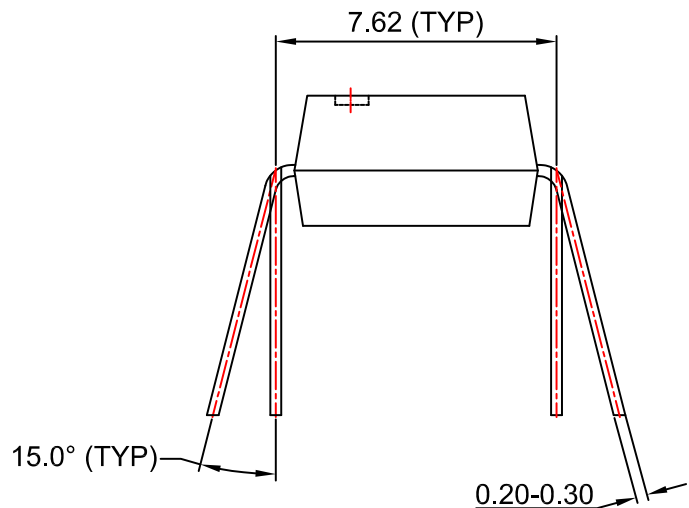
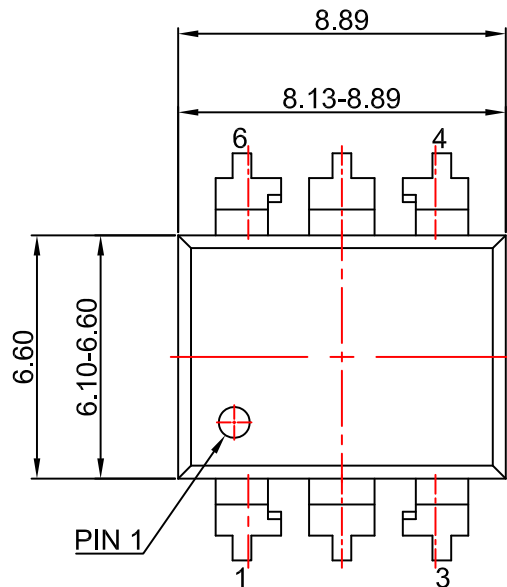
ORDERING INFORMATION

Part Number	Package	Shipping [†]
H11A1M	DIP 6-Pin	50 Units / Tube
H11A1SM	SMT 6-Pin (Lead Bend)	50 Units / Tube
H11A1SR2M	SMT 6-Pin (Lead Bend)	1000 Units / Tape & Reel
H11A1VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	50 Units / Tube
H11A1SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	50 Units / Tube
H11A1SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	1000 Units / Tape & Reel
H11A1TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	50 Units / Tube

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PDIP6 8.51x6.35, 2.54P
CASE 646BX
ISSUE O

DATE 31 JUL 2016



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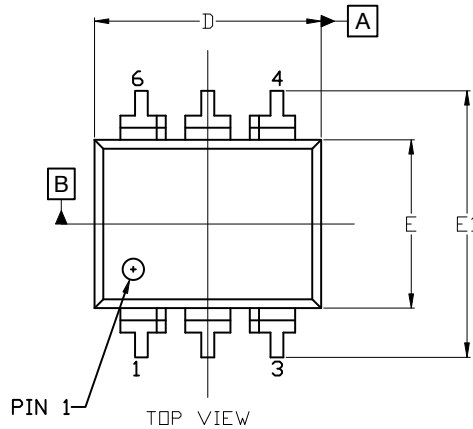
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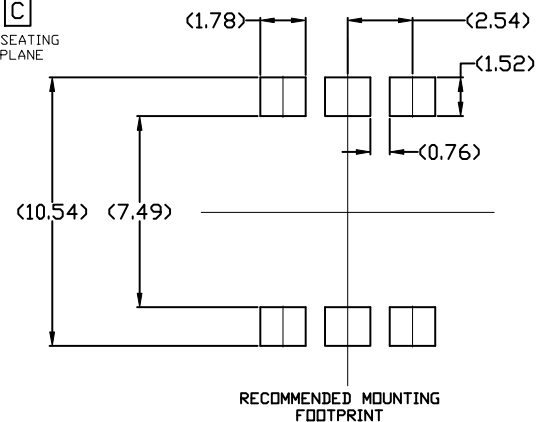
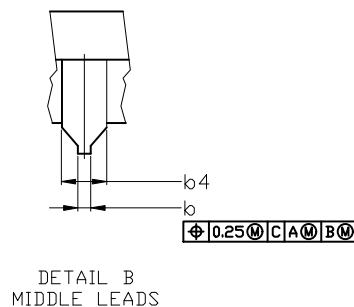
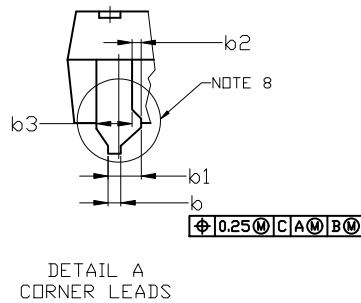
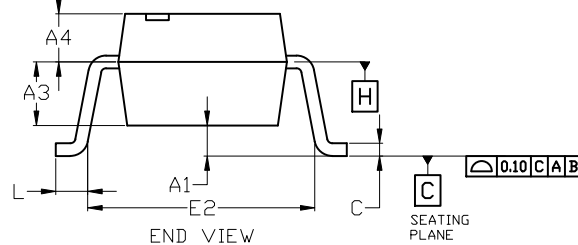
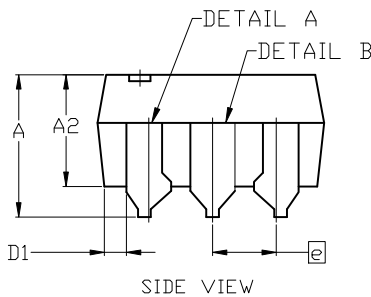
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NOTES:

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5. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).
6. CENTER LINE OF CORNER LEADS IS LOCATED BY LOCATING THE CENTER OF FEATURE b2 AND b3.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	4.80
A1	0.38	---	---
A2	3.28	3.40	3.53
A3	2.49 REF		
A4	1.89 REF		
b	0.41	0.46	0.51
b1	0.76	0.92	1.14
b2	0.25	0.28	0.36
b3	1.02	1.40	1.78
b4	1.778 REF		
c	0.20	0.25	0.30
D	8.13	8.51	8.89
D1	0.86 REF		
E	6.10	6.35	6.60
E1	8.43	9.17	9.90
E2	8.13 REF		
e	2.54 BSC		
L	0.16	0.52	0.88



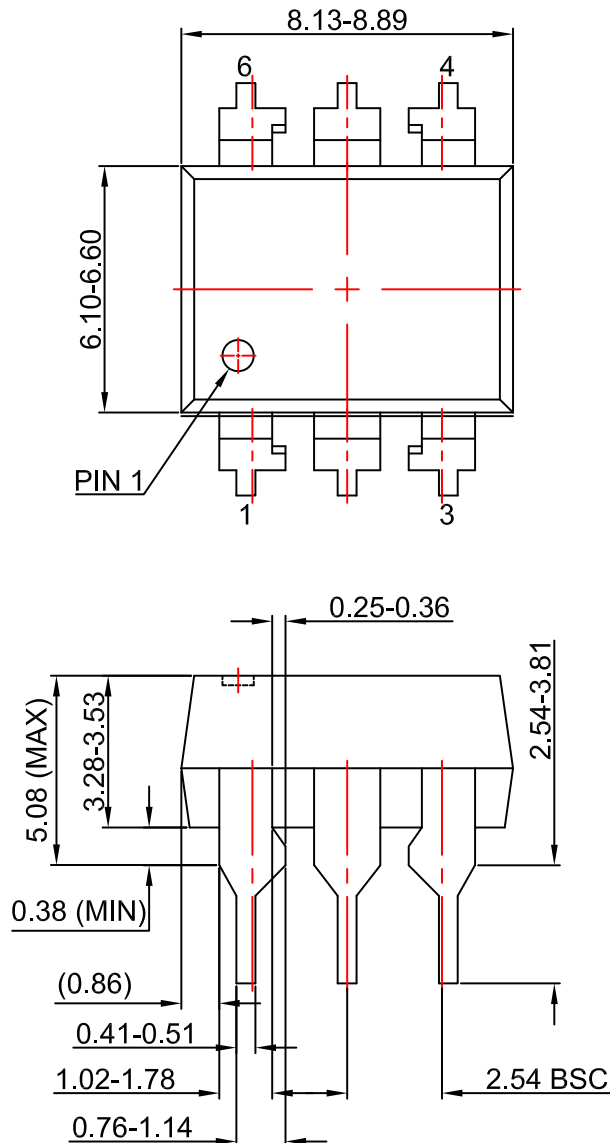
For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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